	Туре	Hits	Search Text	DBs
1	BRS	757	361/93.1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB
2	BRS	4442	current adj (sense sensing) adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	BRS	178	near (MOS MOSFET FET field adjeffect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	BRS	0	near (MOS MOSFET FET field adj	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
5	BRS	36	near (MOS MOSFET FET field adj	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	BRS	4	"5,986,441"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	BRS	5	("4914542" "5004970" "5008586" "5164659" "5220207").PN.	USPAT
8	BRS	10		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
9	BRS	3		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	BRS	12	"5812383" "5814884" "5886383" "5973939").PN.	USPAT
11	BRS	12	("4975821" "5126931" "5331533" "5374857" "5434768" "5734563" "5774350" "5805434" "5812383" "5814884" "5886383" "5973939").PN.	USPAT
12	BRS	12	("4975821" "5126931" "5331533" "5374857" "5434768" "5734563" "5774350" "5805434" "5812383" "5814884" "5886383" "5973939").PN.	USPAT

	Time Stamp	Comments	Error Definition	Errors	Ref #
1	2004/09/01 09:30				s3
2	2004/08/31 09:21				S 4
3	2004/08/31				S5
4	2004/08/31 09:23				S 6
5	2004/08/31 11:29				s7
6	2004/08/31 11:24				S8
7	2004/08/31 11:15				S 9
8	2004/08/31 11:26				S10
9	2004/08/31 11:28				S11
10	2004/08/31 11:26	·			S12
11	2004/08/31 11:27				S13
12	2004/08/31 11:27				S14

	Туре	Hits	Search Text	DBs
13	BRS	2179645	current adj (sense sensing) near across (MOS MOSFET FET field adj effect switch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB
14	BRS	3	near across adj (MOS MOSFET FET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15	BRS	14	adj across adj (MOS MOSFET FET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB
16	BRS	14	near across adj (MOS MOSFET FET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB
17	BRS	5	("4479083" "4502000" "4502001" "4949028" "4967136").PN.	USPAT
18	BRS	22	"5528122".URPN.	USPAT
19	BRS	22	"5528122".URPN.	USPAT
20	BRS	130	near across adj (MOS MOSFET FET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB
21	BRS	92	over adj current and voltage near across adj (MOS MOSFET FET	IIS-PCDIIR · IISDAT ·
22	BRS	11	nielo aoi ellect switch) same	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
23	BRS	5	ITIELO AOI ETTECT SWITCHL AND	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
24	BRS	1	-	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
25	BRS	4	("5530335" "5554919" "5721480" "5736832").PN.	USPAT
26	BRS	3	"6014030".URPN.	USPAT
27	BRS	3	"6014030".URPN.	USPAT

	Time Stamp	Comments	Error Definition	Errors	Ref #
13	2004/08/31				s15
14	2004/08/31 11:42				S16
15	2004/08/31 12:07				S17
16	2004/08/31 12:11				S18
17	2004/08/31 12:09		÷		· S19
18	2004/08/31 12:10				S20
19	2004/08/31 12:10				S21
20	2004/08/31				S22
21	2004/08/31 12:12				S23
22	2004/08/31 12:27				S24
23	2004/08/31 12:35				S25
24	2004/08/31 13:15				S26
25	2004/08/31 12:54				S27
26	2004/08/31 12:56				S28
27	2004/08/31 12:56	,			S29

	Туре	Hits	Search Text	DBs
28	BRS	5	over adj current and voltage near (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
29	BRS	106644	voltage adj across (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
30	BRS	14	voltage adj across adj (MOS MOSFET FET field adj effect switch) and temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
31	BRS	0	voltage adj across adj (MOS MOSFET FET field adj effect switch) same temperature adj (compensating compensate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
32	BRS	502	temperature adj (compensate compensating) adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB
33	BRS	0	temperature adj (compensate compensating) adj resistor same operational adj amplifier same voltage adj drop near (MOS FET MOSFET field adj effect)	EPO; JPO;
34	BRS	0		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
35	BRS	0	temperature adj (compensate compensating) adj resistor and voltage adj drop near (MOS FET MOSFET field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
36	BRS	40	temperature adj (compensate compensating) adj resistor same operational adj amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB
37	BRS	17	compensating) adj resistor same	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB
38	BRS	20	temperature adj (compensate compensating) near resistor same current adj source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
39	BRS	354		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB

	Time Stamp	Comments	Error Definition	Errors	Ref #
28	2004/08/31 13:34				s30
29	2004/08/31 13:34				S31
30	2004/08/31 13:37				S32
31	2004/08/31 13:38	*			s33
32	2004/08/31 13:39				S34
33	2004/08/31 13:40			•	S35
34	2004/08/31 13:40				S36
35	2004/08/31 13:41				s37
36	2004/08/31 15:57	-			S38
37	2004/08/31 16:03				s39
38	2004/08/31 16:25			·	S40
39	2004/08/31 16:25				S41

	Туре	Hits	Search Text	DBs
40	BRS	6	"6,014,030"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
41	BRS	929	324/713	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
42	BRS	187		US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
43	BRS	95	current adj (limit limiting) and switch near across near voltage and (MOS MOSFET field adj effect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
44	BRS	28		US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
45	BRS	28	current adj (limit limiting) and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
46	BRS	0	current adj (limit limiting) near transistor and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
47	BRS	0	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and switch near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
48	BRS	8	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across near voltage and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT

	Time Stamp	Comments	Error Definition	Errors	Ref #
40	2004/09/01 10:25				S1
41	2004/09/01 10:32				S2
42	2004/12/06 15:48				S42
43	2004/12/06 15:48				S43
44	2004/12/06 15:49				S44
45	2004/12/06 15:54				S45
46	2004/12/06 15:55				S46
47	2004/12/06 15:56				S47
48	2004/12/06 15:57				S48

	Туре	Hits	Search Text	DBs
49	BRS	53	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across and (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
50	BRS	1	current adj (limit limiting) near (transistor MOS MOSFET field adj effect) and voltage near across near (MOS MOSFET field adj effect) and voltage adj (divider shunt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
51	BRS	3		US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT

	Time Stamp	Comments	Error Definition	Errors	Ref #
49	2004/12/06 15:58				S49
50	2004/12/06 16:02				S50
51	2004/12/06 16:04				S51